

SMT PHEMT LOW NOISE AMPLIFIER, 17 - 26 GHz

Typical Applications

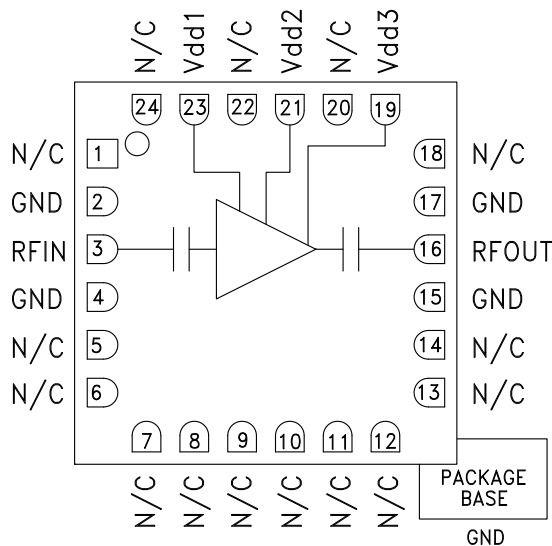
The HMC517LC4 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military

Features

- Noise Figure: 2.5 dB
- Gain: 19 dB
- OIP3: +23 dBm
- Single Supply: +3V @ 67 mA
- 50 Ohm Matched Input/Output
- RoHS Compliant 4 x 4 mm Package

Functional Diagram



General Description

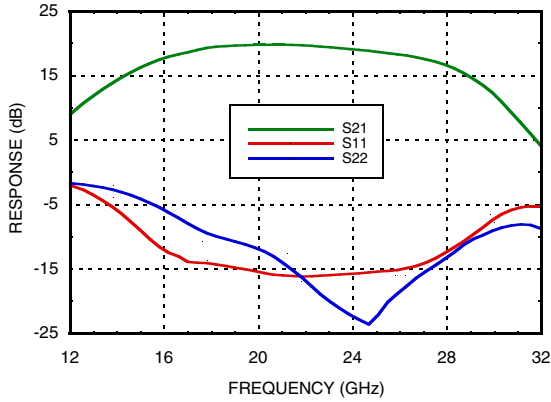
The HMC517LC4 chip is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier (LNA) housed in a leadless “Pb free” RoHS compliant SMT package. The HMC517LC4 provides 19 dB of small signal gain, 2.5 dB of noise figure and has an output IP3 of +23 dBm. The P1dB output power of +13 dBm enables the LNA to also function as a LO driver for balanced, I/Q or image reject mixers. The HMC517LC4 allows the use of surface mount manufacturing techniques.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd\ 1, 2, 3} = +3\text{V}$

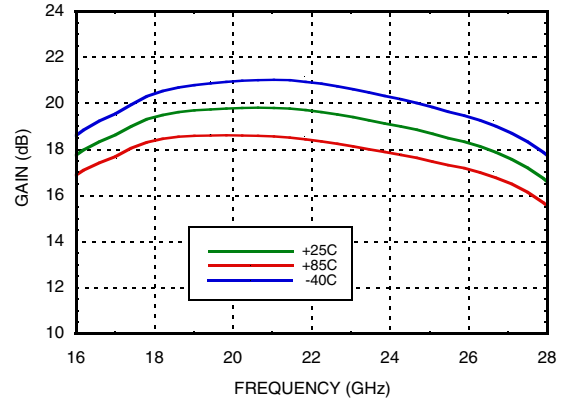
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range	17 - 22		22 - 26				GHz
Gain	16	19		15	18		dB
Gain Variation Over Temperature		0.02	0.03		0.02	0.03	dB/ °C
Noise Figure		2.5	3.1		2.6	3.3	dB
Input Return Loss		15			15		dB
Output Return Loss		11			17		dB
Output Power for 1 dB Compression (P1dB)		12			13		dBm
Saturated Output Power (P _{sat})		15			16		dBm
Output Third Order Intercept (IP3)		23			24		dBm
Supply Current (I _{dd})(V _{dd} = +3V)		67			67		mA

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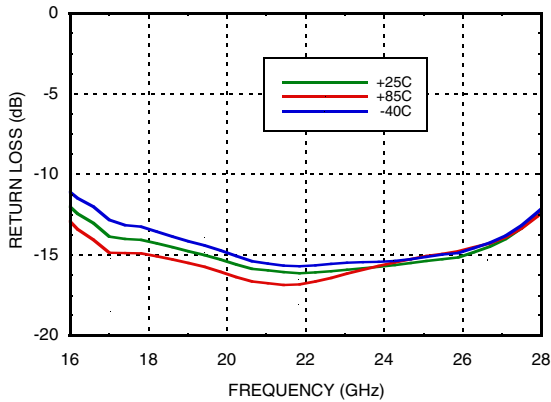
Broadband Gain & Return Loss



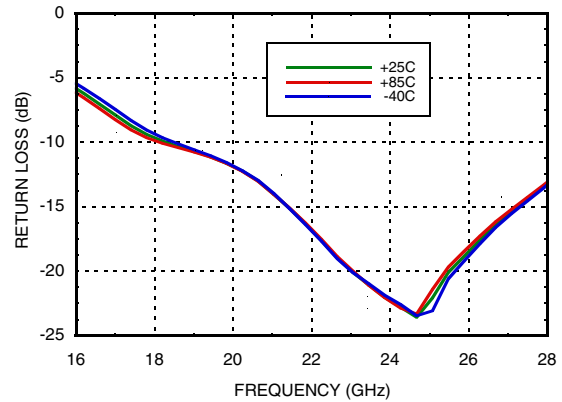
Gain vs. Temperature



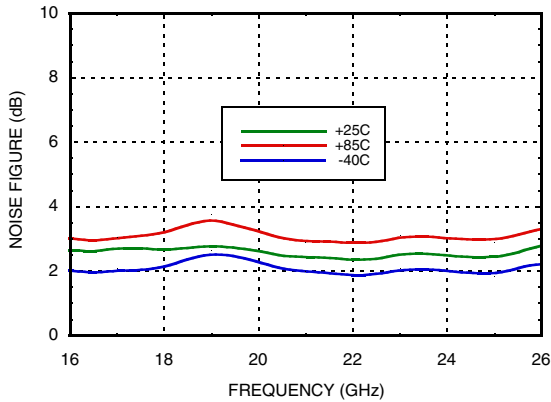
Input Return Loss vs. Temperature



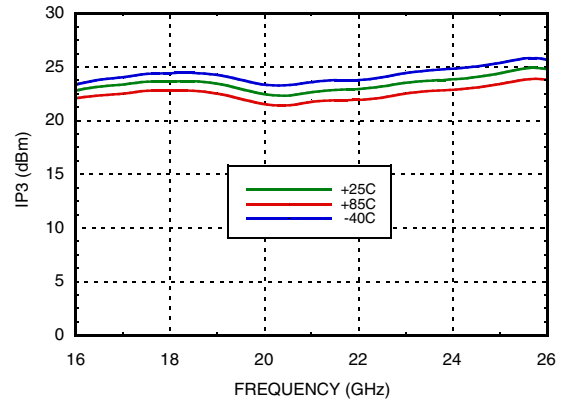
Output Return Loss vs. Temperature



Noise Figure vs. Temperature

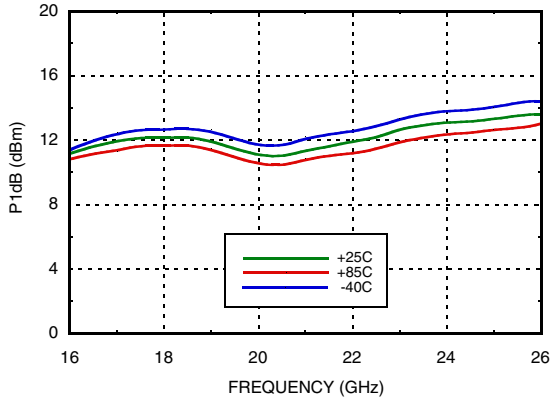


Output IP3 vs. Temperature

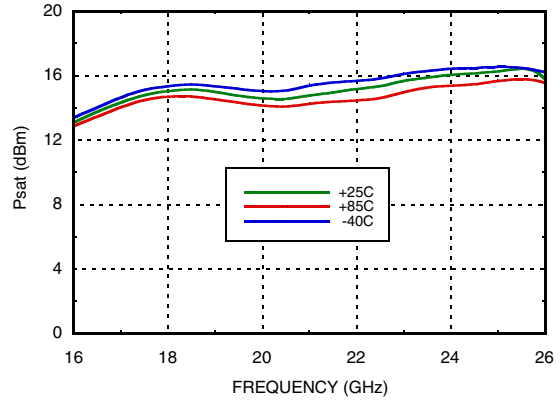


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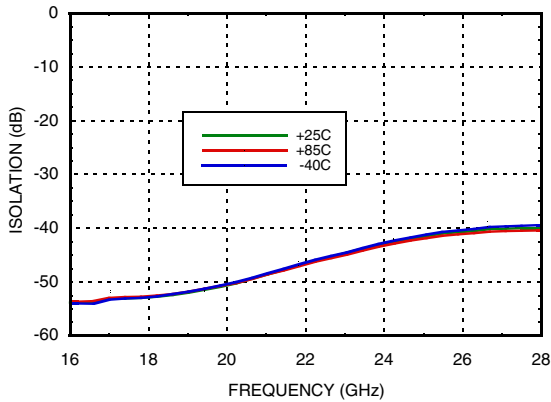
P1dB vs. Temperature



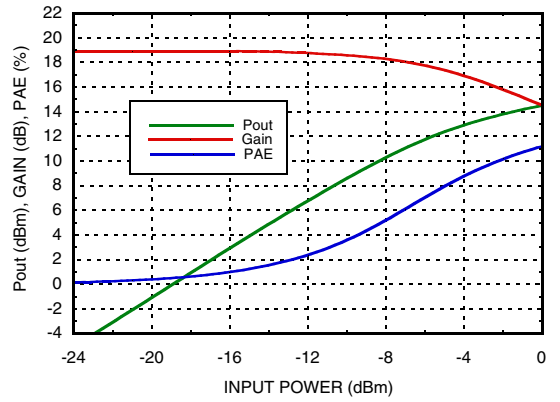
Psat vs. Temperature



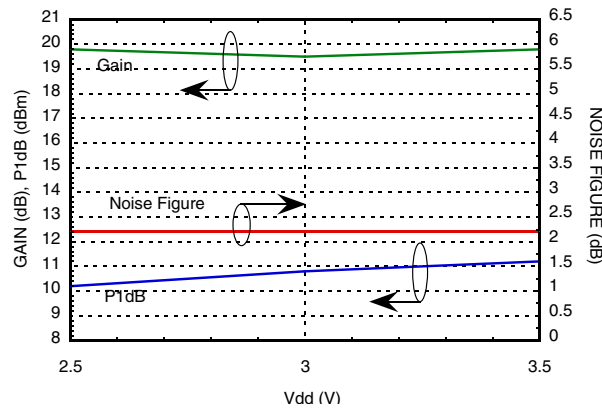
Reverse Isolation vs. Temperature



Power Compression @ 21 GHz



Gain, Noise Figure & Power vs. Supply Voltage @ 21 GHz



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Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+5.5 Vdc
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	+14 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 13 mW/°C above 85 °C)	1.2 W
Thermal Resistance (channel to die bottom)	76.9 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

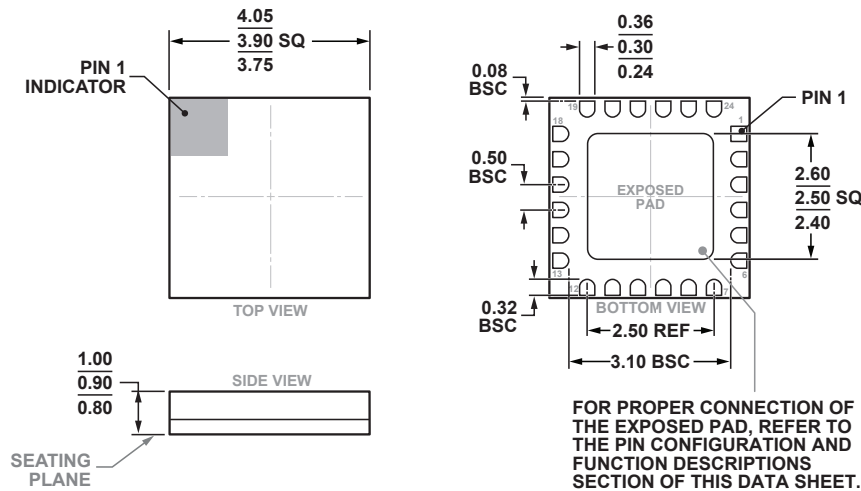
Vdd (V)	Idd (mA)
+2.5	66
+3.0	68
+3.5	71

Note: Amplifier will operate over full voltage range shown above.



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



24-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-24-1)

Dimensions shown in millimeters.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC517LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H517 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5 - 14, 18, 20, 22, 24	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN ○ — —
23, 21, 19	Vdd1, 2, 3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	○ Vdd1,2,3
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	— — ○ RFOUT
2, 4, 15, 17	GND	These pins and package bottom must be connected to RF/DC ground.	○ GND

Application Circuit

Component	Value
C1, C2, C3	100 pF
C4, C5, C6	1,000 pF
C7, C8, C9	2.2 μF

